

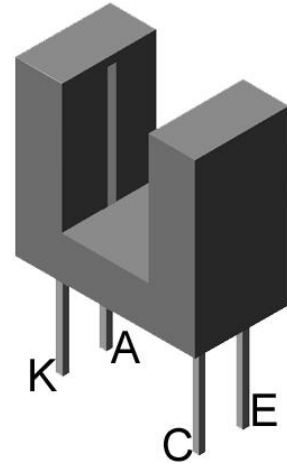
## ST150E

### ■ Features

- Combines high output GaAs IRED with high sensitive phototransistor.
- No contact detecting manner
- Slit width(resolution):0.8mm
- Meet RoHS

### ■ Applications

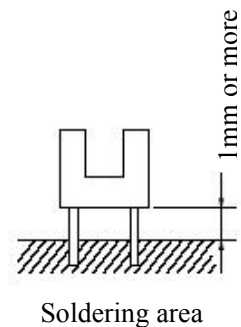
- Facsimiles
- Printers
- Copiers
- Opto-electronic switch
- Ticket vending machine



### ■ Absolute Maximum Ratings

(Ta=25°C)

Item		Symbol	Rating	Unit
Input	Farward Current	IF	50	mA
	Reverse Voltage	Vr	6	V
	Power Dissipation	P	75	mW
	Forward Peak Current*1	IFP	1	A
Output	Collector-Emitter Voltage	Vceo	30	V
	Emitter-Collector Voltage	Veco	6	V
	Collector power dissipation	Pc	50	mW
Operating Temperature*2		Topr	-20~+65	°C
Storage Temperature		Tstg	-30~+75	°C
Soldering Temperature*3		Tsol	260	°C



\*1. Pules Width ≤ 100 μs, Duty ratio=1%

\*2. Higher operating temperature could be met according to our client's requirement.

\*3. Soldering time ≤ 5s

### ■ Electro-Optical Characteristics

(Ta=25°C)

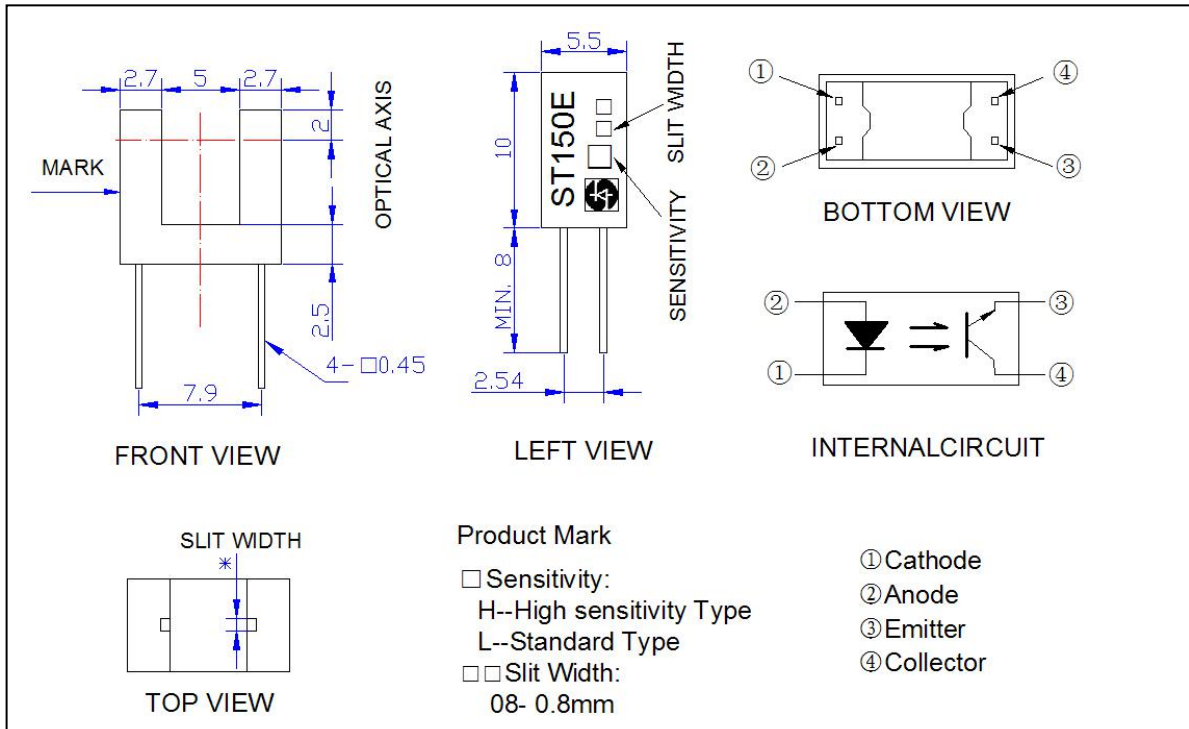
Item		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Farward Voltage	VF	IF=20mA	-	1.25	1.5	V
	Reverse Current	IR	VR=3V	-	-	10	μA
	Peak Wavelength	λp	IF=20mA	-	940	-	nm
Output	Dark Collector Current	Iceo	Vce=20V	-	-	1	μA
	Light Collector Current	ST150EL08	Vce=5V IF=8 mA	0.25	-	-	mA
		ST150EH08		4	-	-	
	Peak Wavelength	λp		-	860	-	nm
Collector-Emitter Saturation voltage	VCE	IF=8 mA Ic=0.15mA	-	-	0.4	V	
Transfer Characteristics	Response Time	Tr	IF=20mA Vce=5V	-	5	-	μS
		Tf	Rc=100Ω	-	5	-	μS

## Material

Type	IR	PT	Lead Frame	Wire	Part Package	Holder
Material	GaAs	Silicon	SPCC	Gold	Epoxy	ABS*

\*other materials of holder can be met according to our client' requirement

## Dimensions



## Applications

